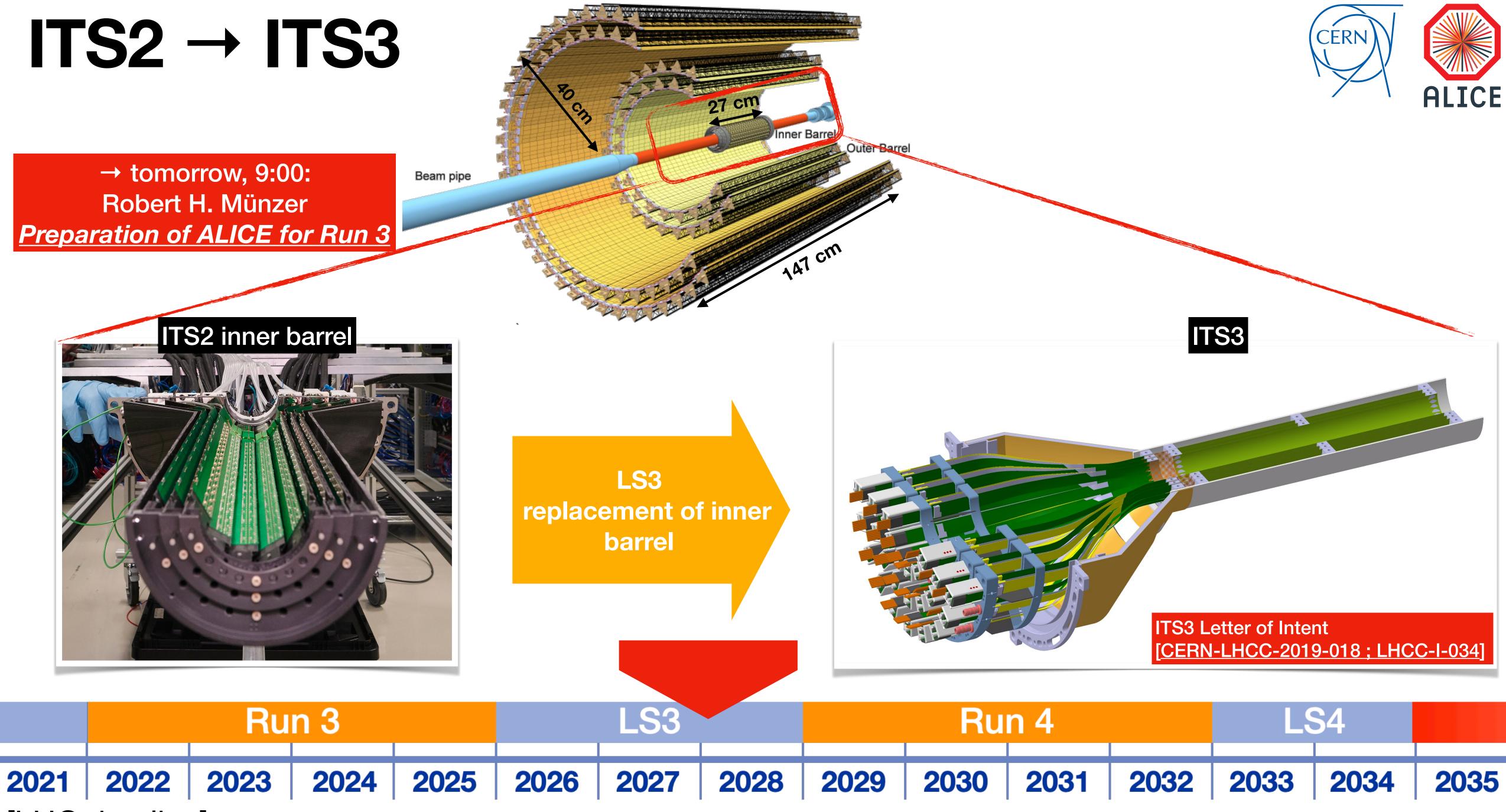


A truly cylindrical inner tracker for ALICE Magnus Mager (CERN) on behalf of the ALICE collaboration



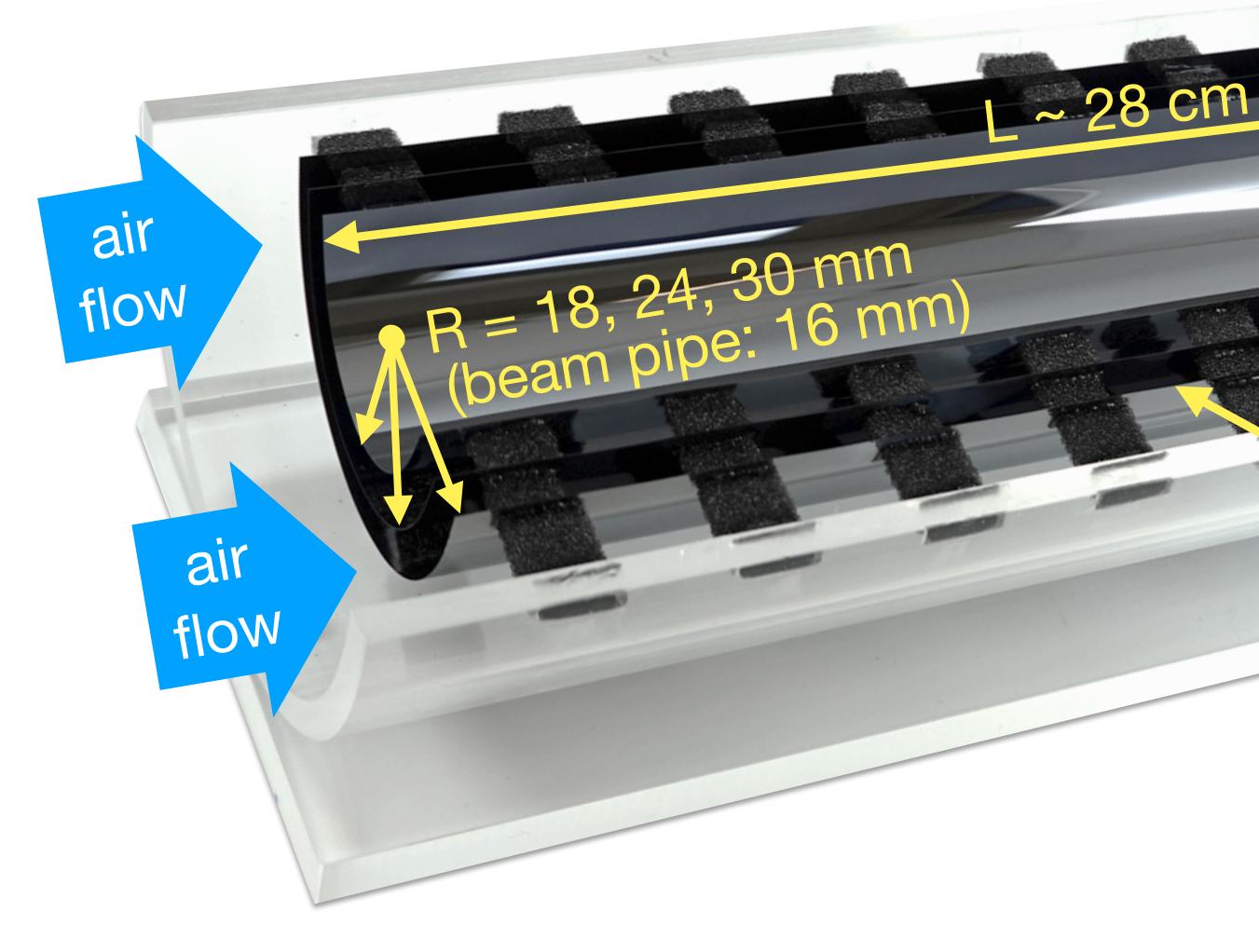




[LHC timeline]



ITS3 detector concept (1) mechanical mockup using silicon dummies





carbon foam

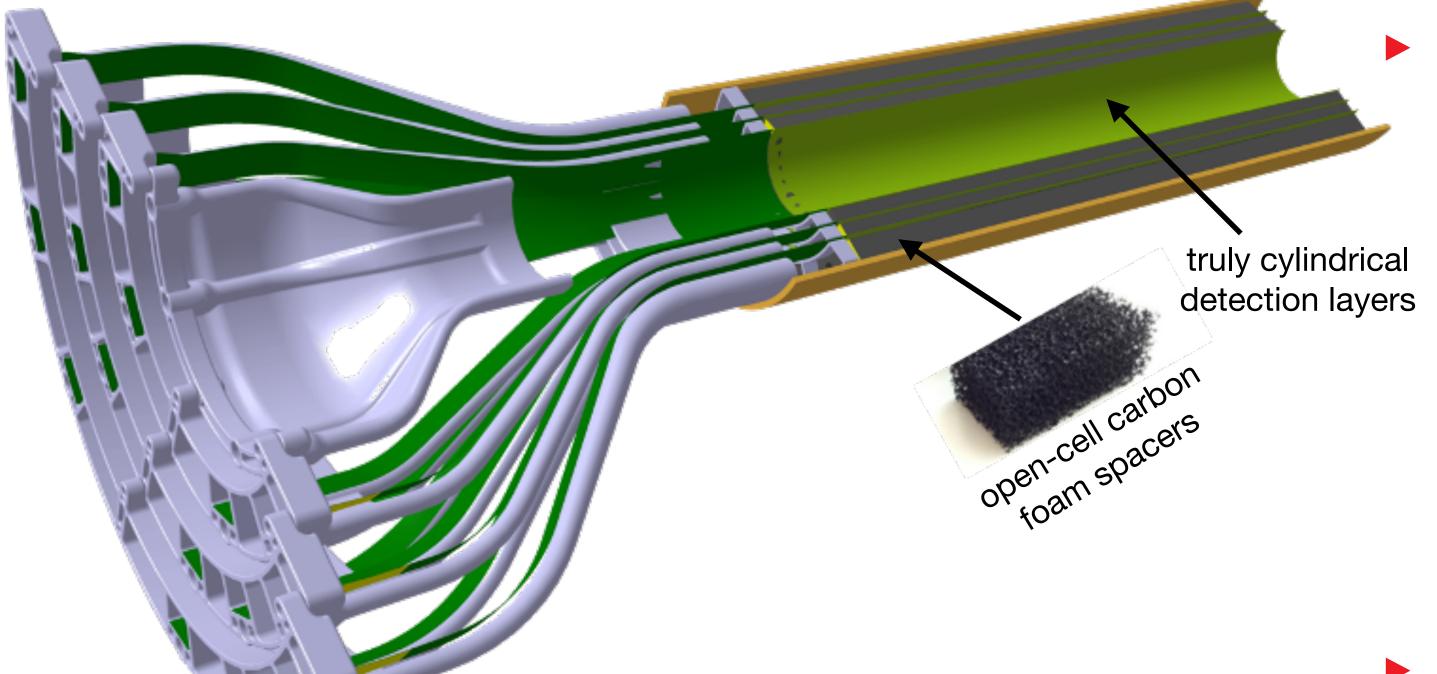
3 sensors (MAPS) wafer-scale (stitched) thinned to O(20-40) µm bent to cylindrical shape







ITS3 detector concept (2)



| Beam pipe Inner/Outer Radius (mm) | | 16.0/16.5 | |
|--|------------|-------------|----------|
| IB Layer Parameters | Layer 0 | Layer 1 | Layer 2 |
| Radial position (mm) | 18.0 | 24.0 | 30.0 |
| Length (sensitive area) (mm) | | 300 | |
| Pseudo-rapidity coverage | ±2.5 | ±2.3 | ±2.0 |
| Active area (cm ²) | 610 | 816 | 1016 |
| Pixel sensor dimensions (mm ²) | 280 x 56.5 | 280 x 75.5 | 280 x 94 |
| Number of sensors per layer | | 2 | |
| Pixel size (μm²) | | O (10 x 10) | |





Key ingredients:

- 300 mm wafer-scale sensors, fabricated using stitching
- thinned down to 20-40 µm (0.02-0.04% X₀), making them flexible
- bent to the target radii
- mechanically held in place by carbon foam ribs
- Key benefits:
 - extremely low material budget: 0.02-0.04% X₀
 - (beampipe: 500 μ m Be: 0.14% X₀)
 - homogeneous material distribution: negligible systematic error from material distribution

The whole detector will consist of six (!) sensors (current ITS IB: 432) – and barely anything else

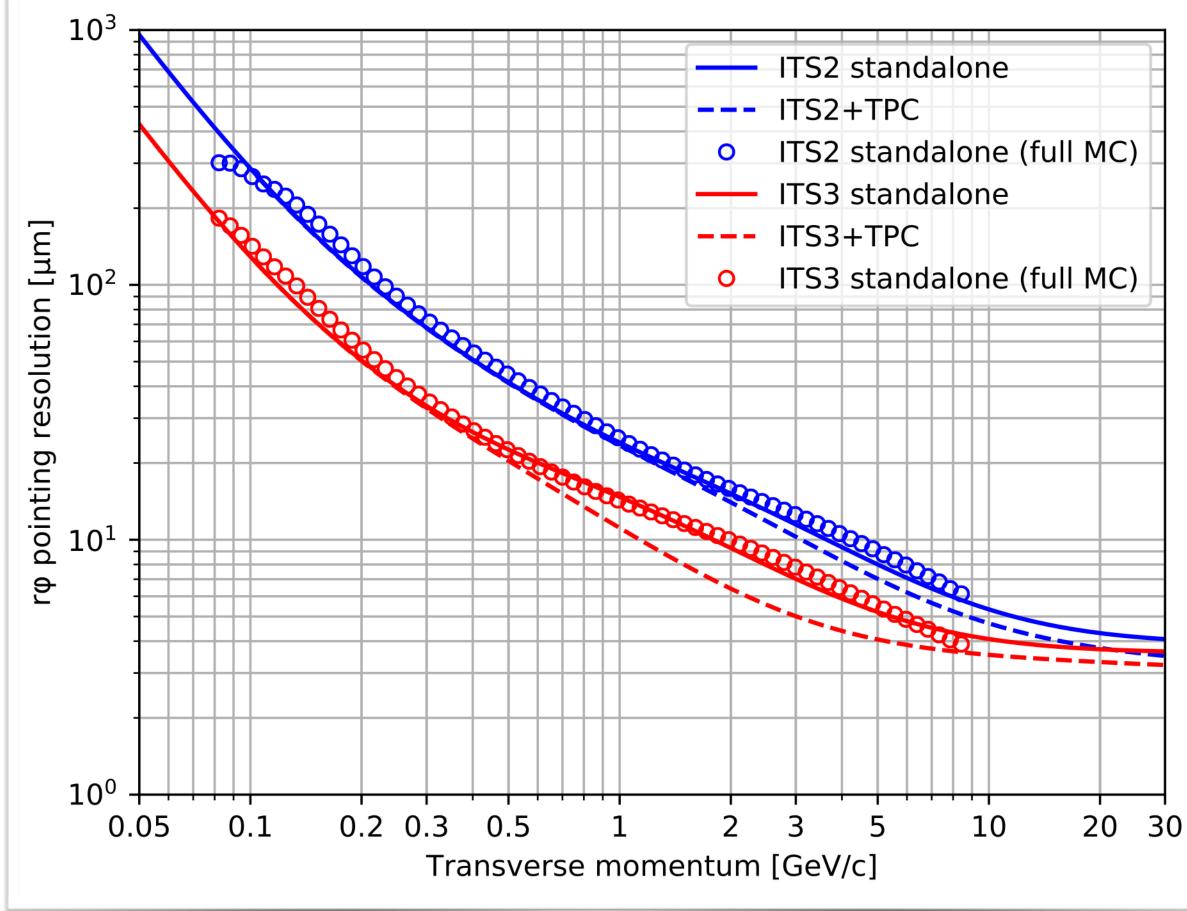
| ver 2 | |
|-------|--|
| | |
| 0 | |
| 0 | |
| 0 | |





Performance improvement

pointing resolution



[ALICE-PUBLIC-2018-013]

improvement of factor 2 over all momenta



- Improvement of pointing resolution by:
 - drastic reduction of material budget (0.3 \rightarrow 0.05% X₀/layer)
 - being **closer** to the interaction point $(24 \rightarrow 18 \text{ mm})$
 - thinner and smaller and **beam pipe** (700 \rightarrow 500 µm; 18 \rightarrow 16 mm)
- Directly boosts the ALICE core physics program that is largely based on:
 - low momenta
 - secondary vertex reconstruction
- E.g. Λ_c S/B improves by factor 10, significations by factor 4



Main R&D lines towards ITS3

Ultra-light mechanics and cooling

- mechanical concept to hold thin sensors "without" material
 - development of assembly procedure
 - qualification of carbon foams
- verification and optimisation of air cooling concept

Thinning, bending, interconnection

- development of procedures to handle and bend large thin chips
- characterisation of electrical and mechanical properties of sensors after bending
- development of electrical interconnection to bent chips



Wafer-scale sensor development

- switch to 65 nm technology (TPSCo)
 - verification of the technology for radiation tolerance and charge collection
- stitched sensor design
 - chip architecture
 - optimisation for yield





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Bending of wafer-scale sensors procedure

R = 30 mm (layer 2)50 µm silicon



Com?



Bending of wafer-scale sensors procedure

HERHEITSGEFÅS

R = 30 mm (layer 2) 50 µm silicon

Magnus Mager (CERN) | ALICE ITS3 | ICHEP



Bending of wafer-scale sensors procedure

ERHEITSGEFASS

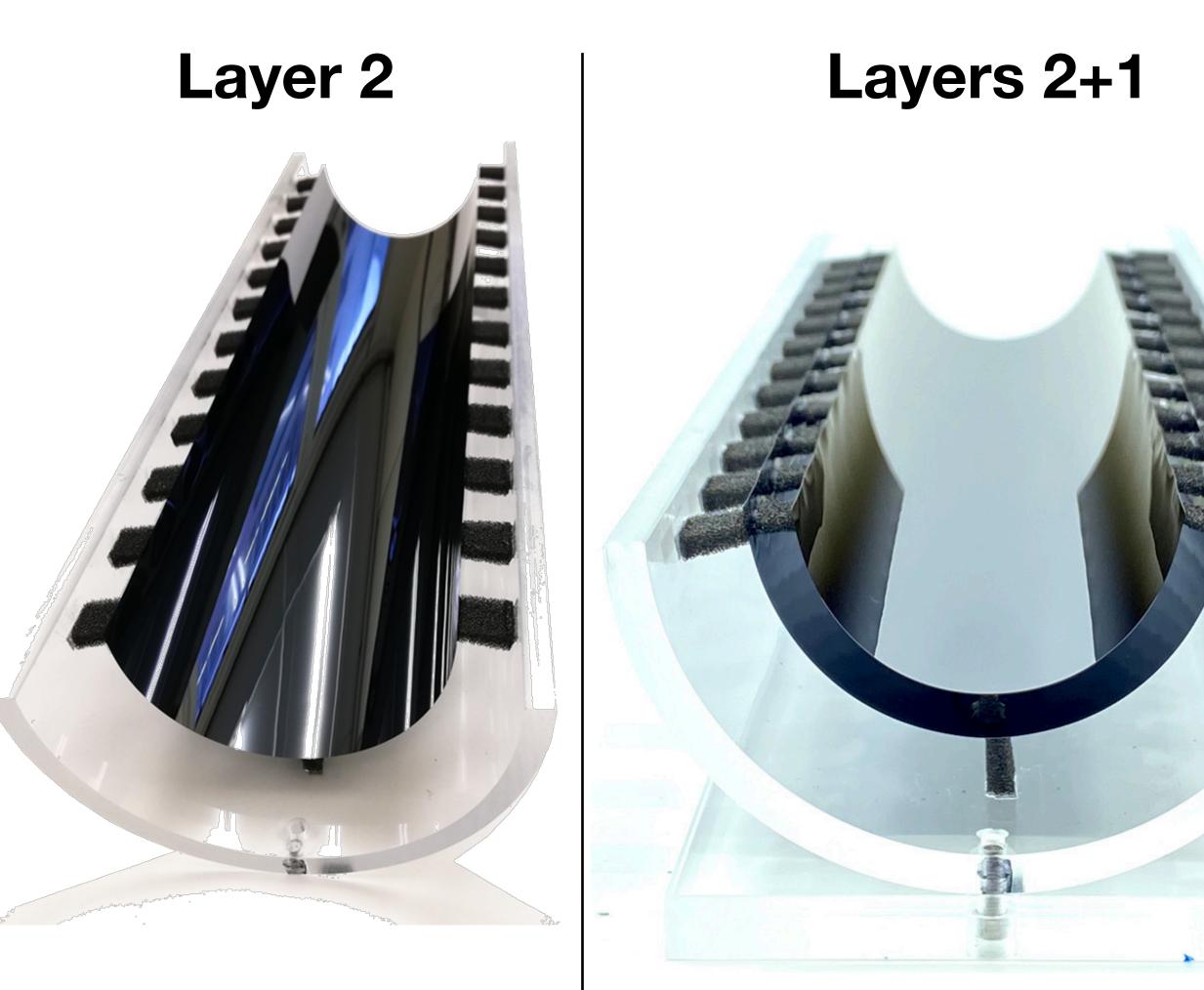
R = 30 mm (

50 um silicon





Layer assembly



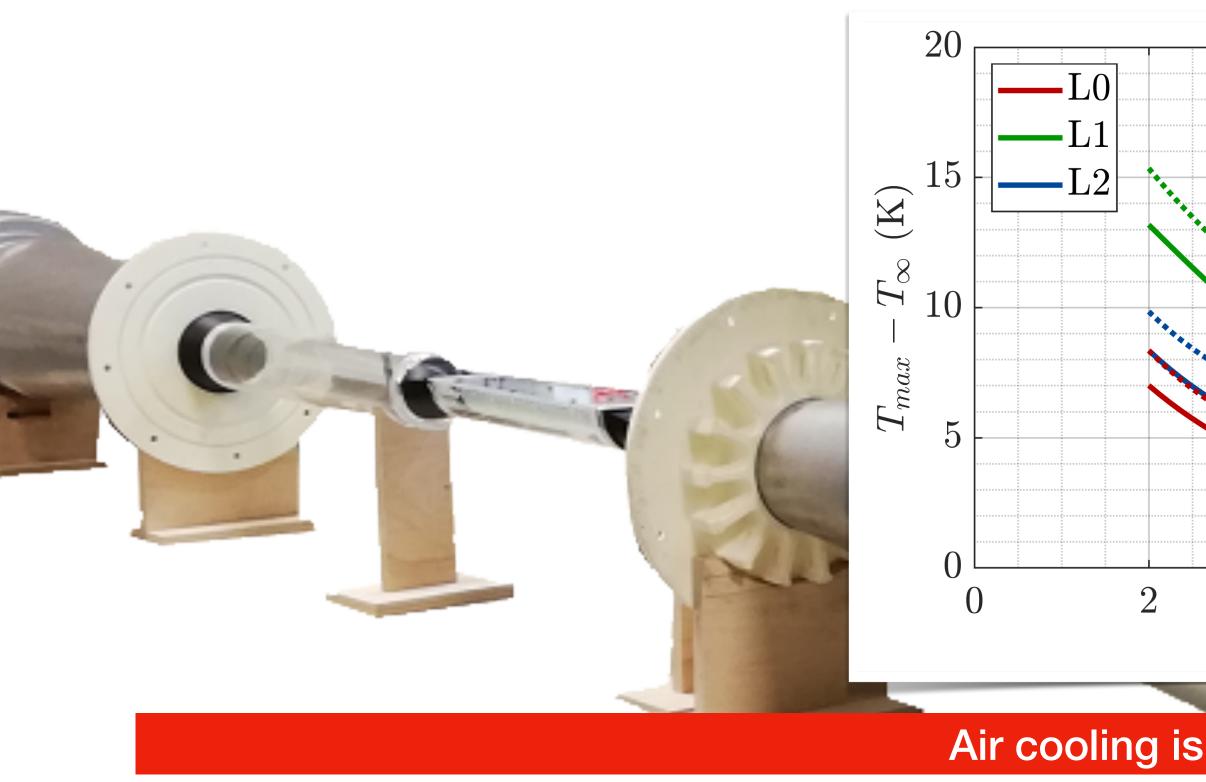


Mechanically, the integration is very feasible – now the assemblies are characterised and optimised

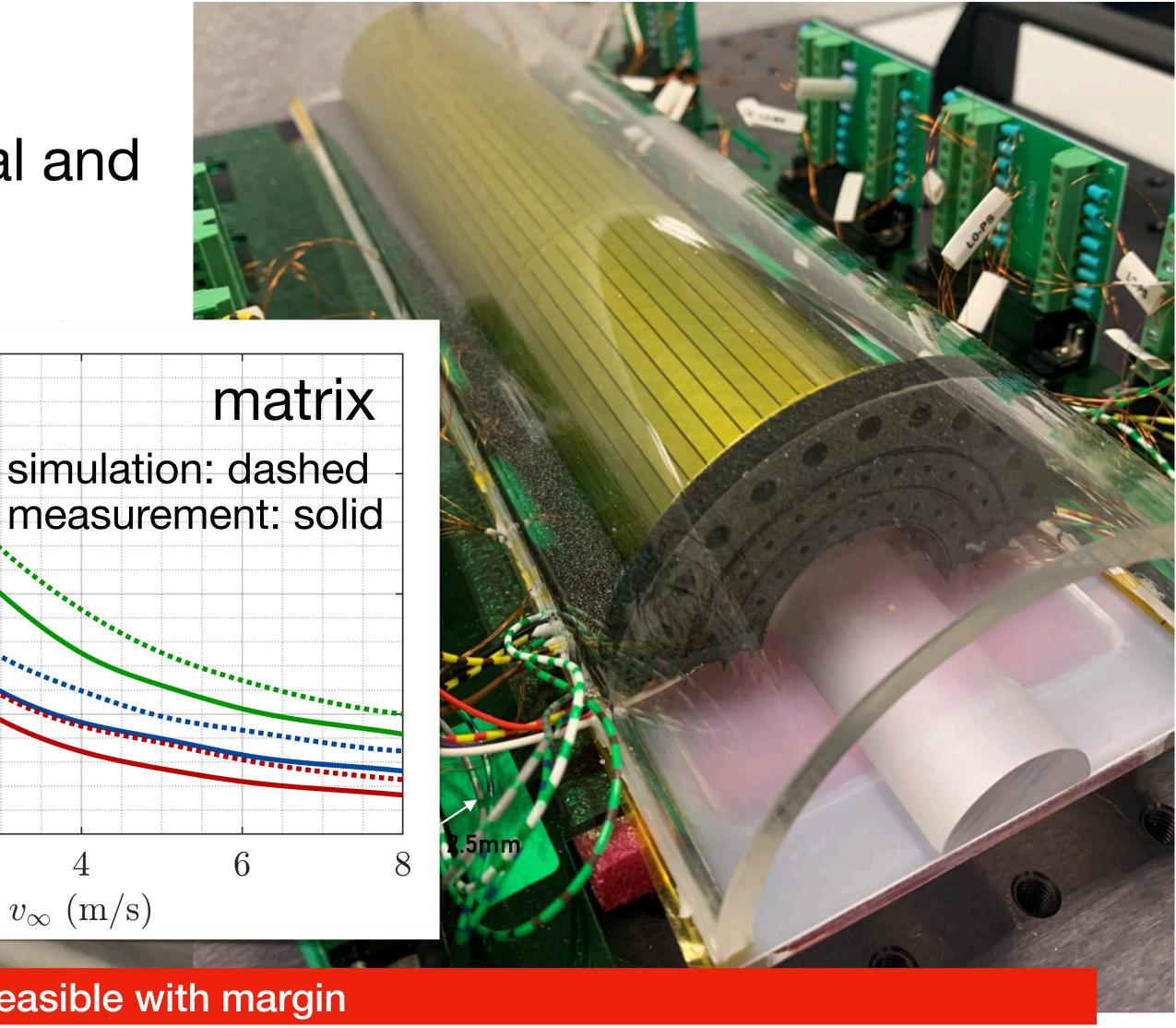


R&D on air cooling

- A set of models based on heating elements are being developed
- Placed in a custom wind tunnel, thermal and mechanical properties are studied







Air cooling is feasible with margin



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Wafer-scale sensor development

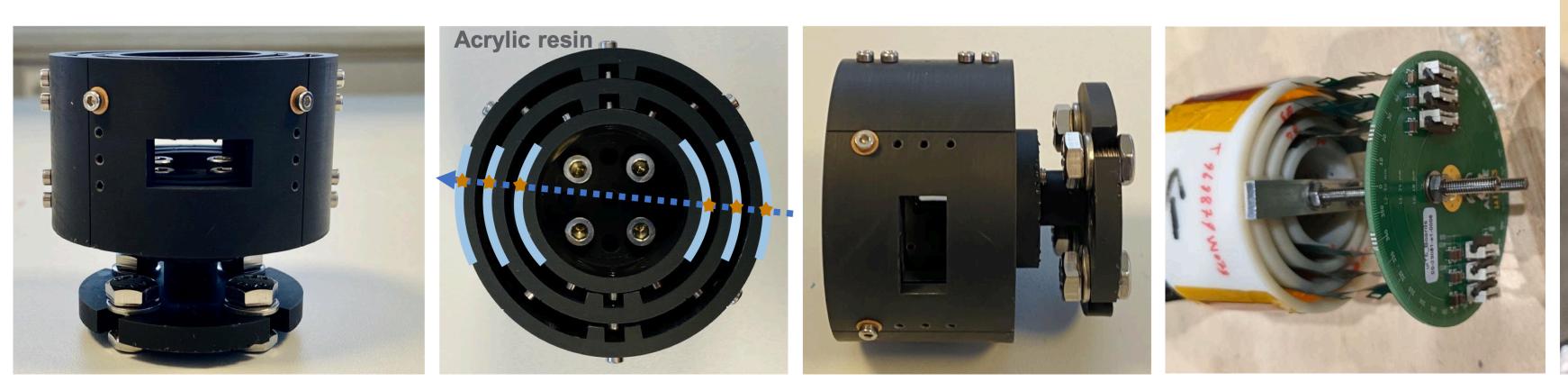
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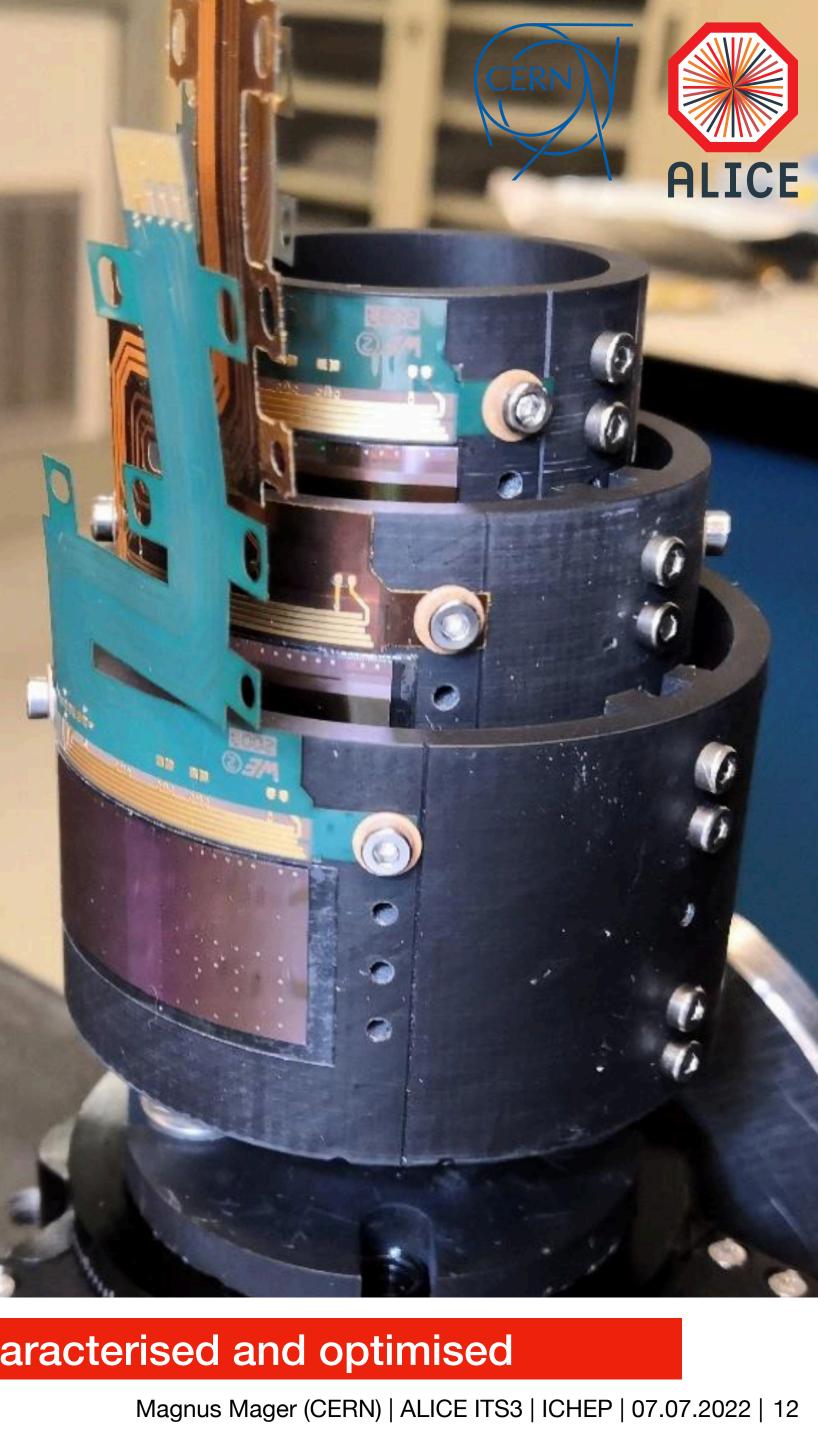




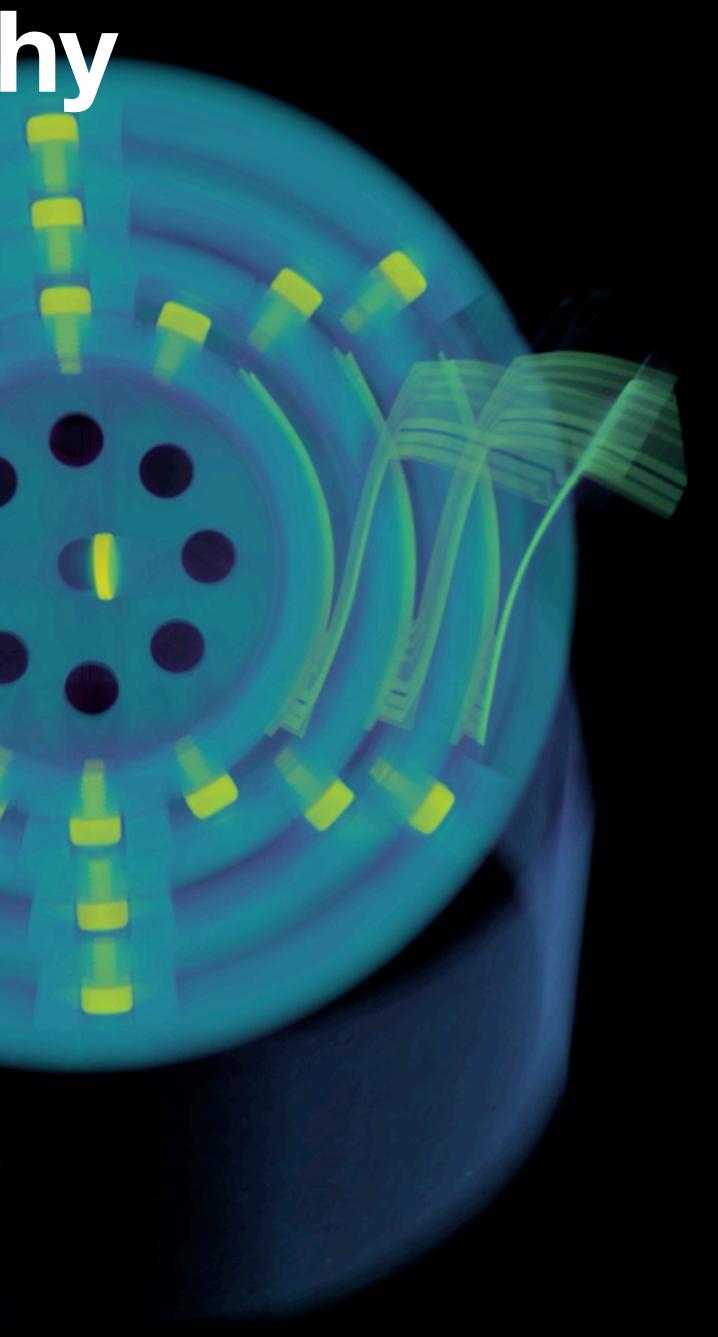
Bent ALPIDEs [doi:10.1016/j.nima.2021.166280]

- Functional chips (ALPIDEs) are bent routinely
 - several different ways were explored -(bending before bonding, or vice versa, different jigs)
 - all radii of ITS3 are easily achievable
- Chips continue to work
 - tested at several beam campaigns
- By now, we have a full mock-up of the final ITS3, called "µITS3"
 - 6 ALPIDE chips, bent to the target radii of ITS3





Mechanically, the integration is very feasible – now the assemblies are characterised and optimised









(Cu target)





(Cu target)

181

<u>sonn</u>



beam



(Cu target)

6

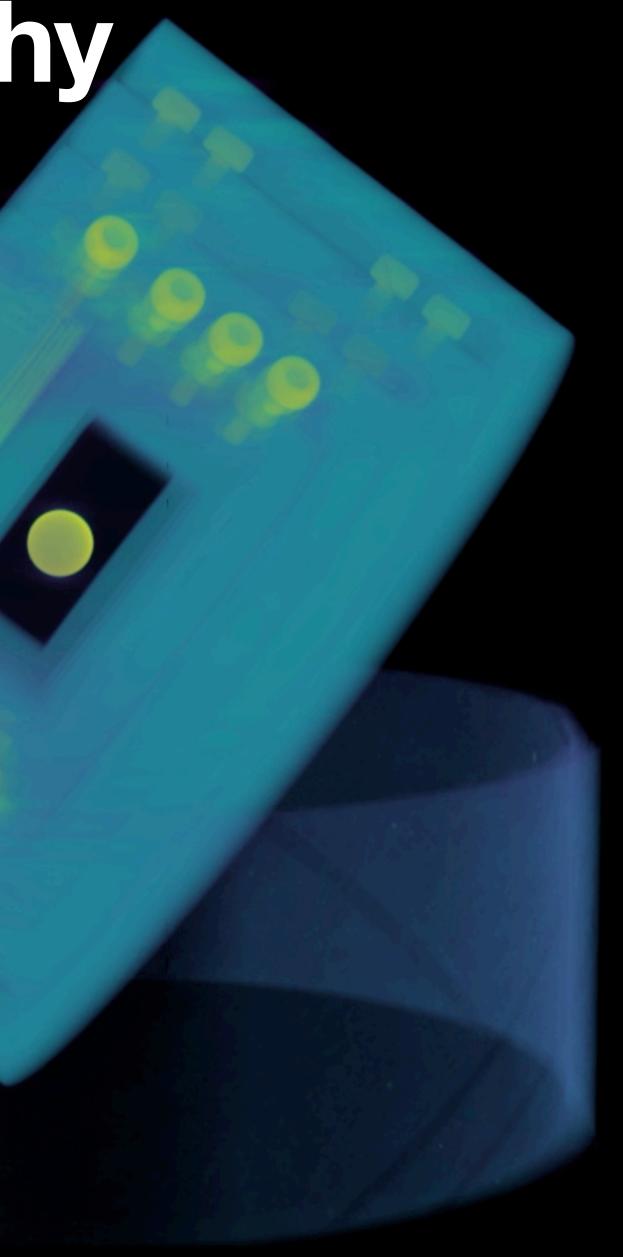
<u>sonn</u>













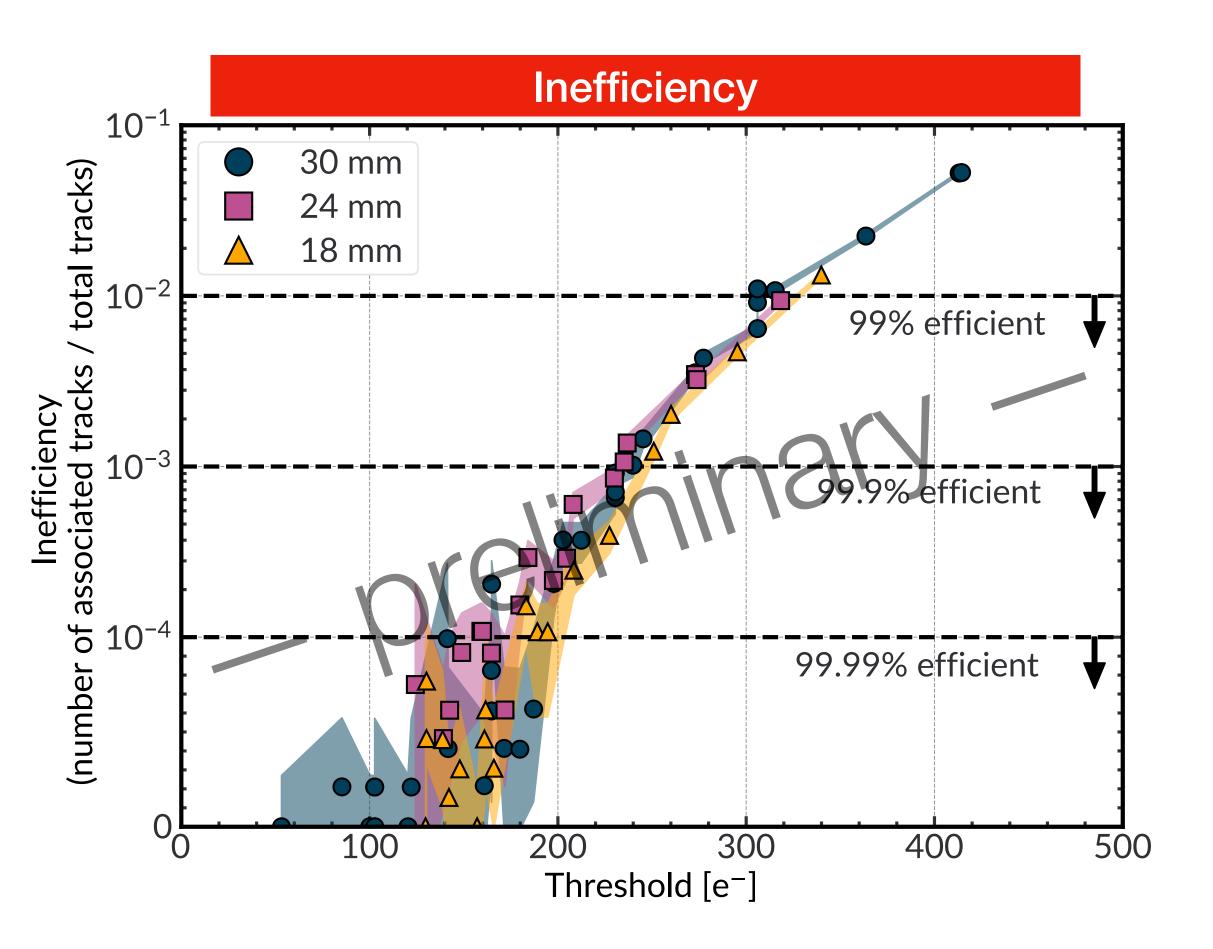


beam window (only Si)

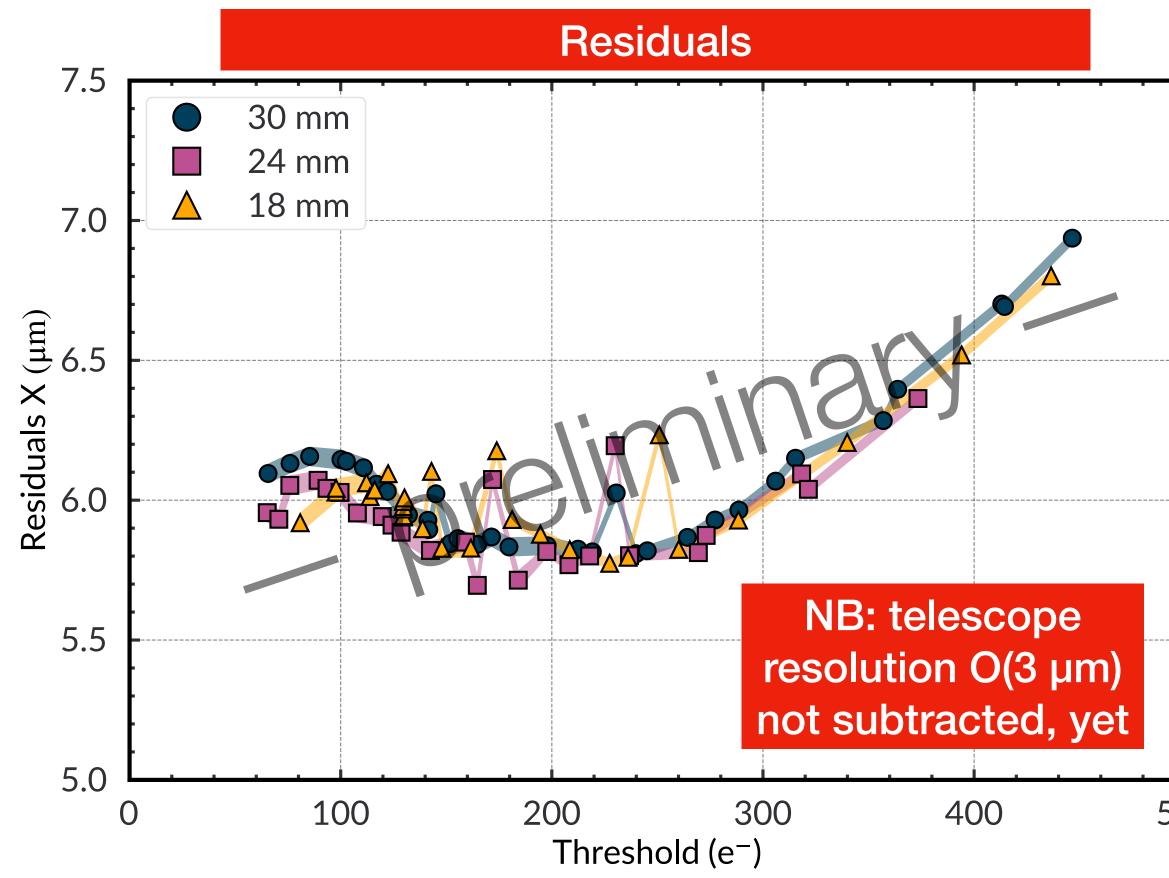




Bent ALPIDEs – beam test results at all nominal ITS3 radii

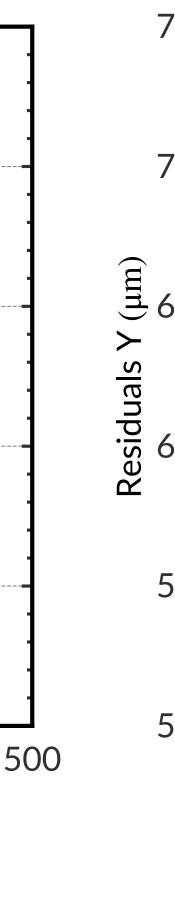






Bent MAPS "just" continue to work! – bending is not visible in main performance figures







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Wafer-scale sensor development

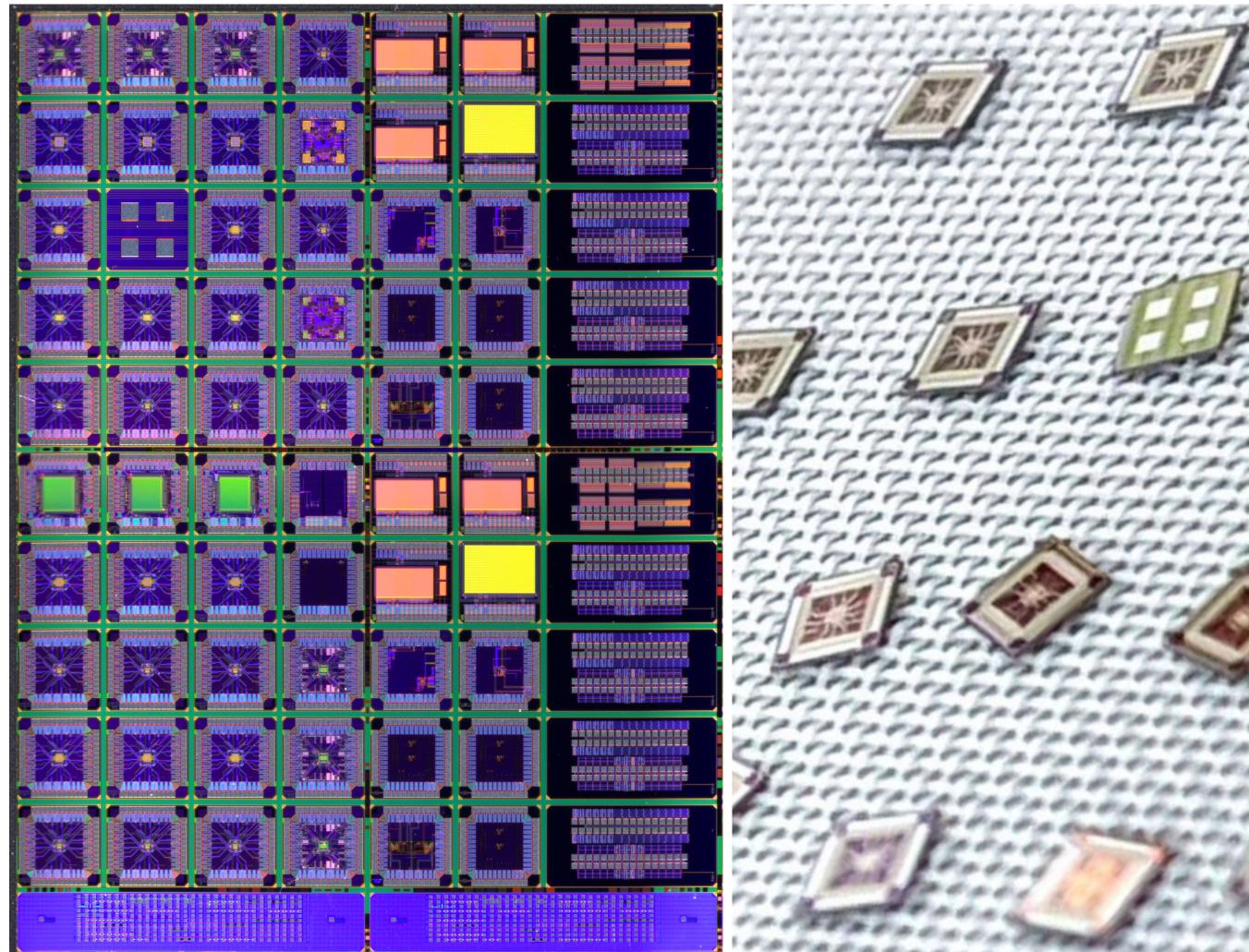
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Sensor design: advancing the technology CERN qualifying the TPSCo 65 nm CMOS Imaging Technology

- Together with CERN EP R&D
- Leverages on experience with 180 nm process (ALICE ITS2 an beyond)
 - excellent links to foundry
- Comprehensive first submission: **55** prototype chips
 - different processing flavours were tried
- Immense dataset for ITS3 and the community at large

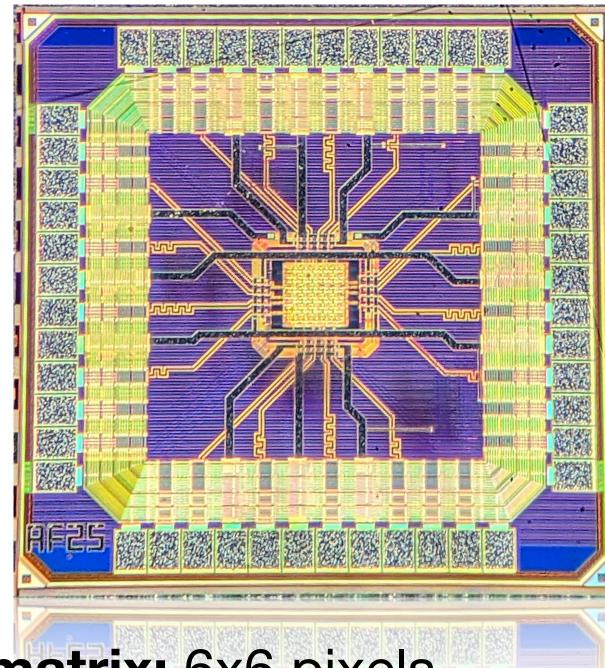


This technology has a large potential for the field, not only because it is done on 300 mm wafers!



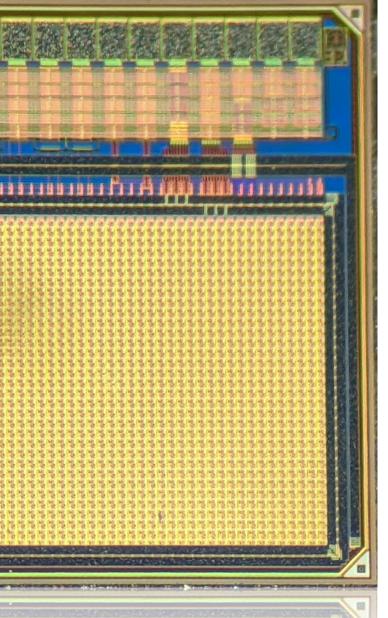


Pixel prototype chips (selection) APTS CE65



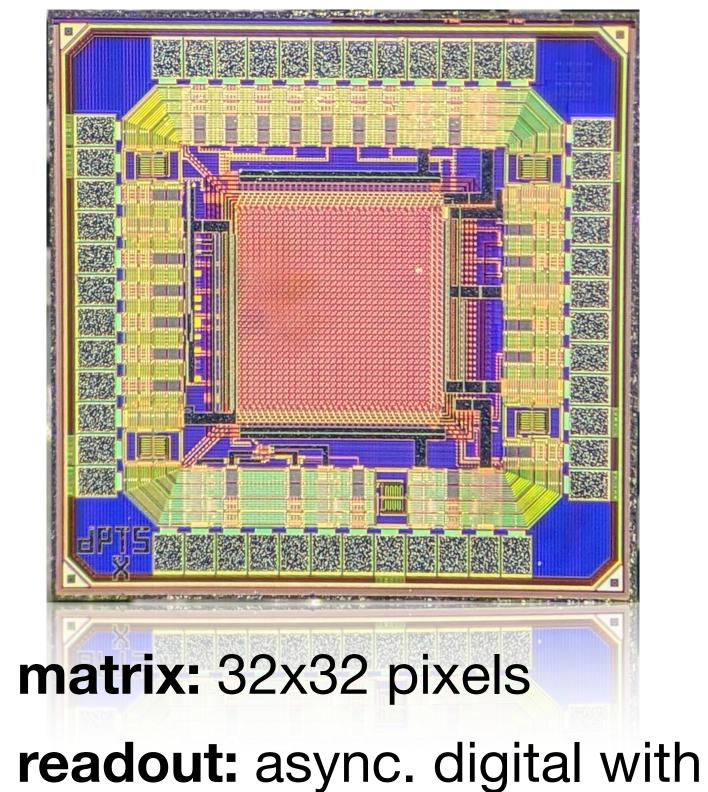
- matrix: 6x6 pixels
- readout: direct analog readout of central 4x4
- **pitch:** 10, 15, 20, 25 μm
- total: 34 dies

- matrix: 64x32, 48x32 pixels
- readout: rolling shutter analog
- **pitch:** 15, 25 μm
- total: 4 dies





DPTS



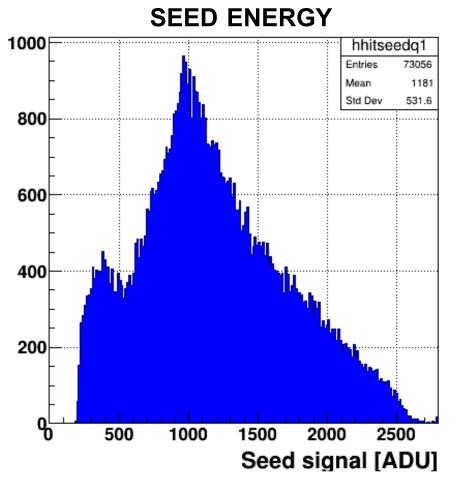
- matrix: 32x32 pixels
- ΤοΤ
- pitch: 15 µm
- total: 3 dies

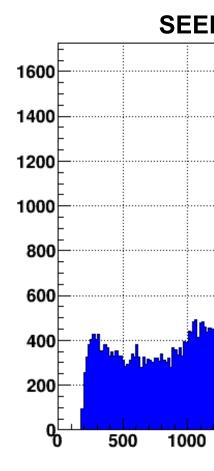
Comprehensive set of prototypes and variants to explore the technology for particle detection

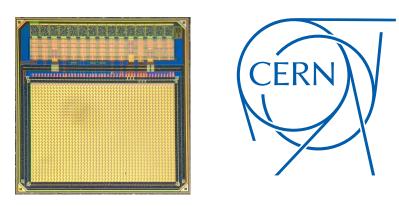


CE65 – Fe-55 lab tests charge sharing **BASIC DIODE [A4]:**

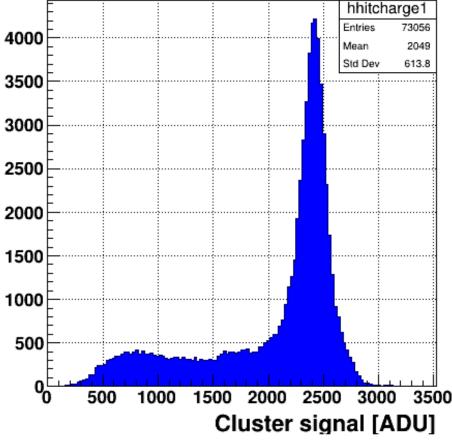
- Very good charge collection properties
- Effect of different optimisation can be seen very clearly
- Now being also verified
 - after irradiation
 - in beam tests

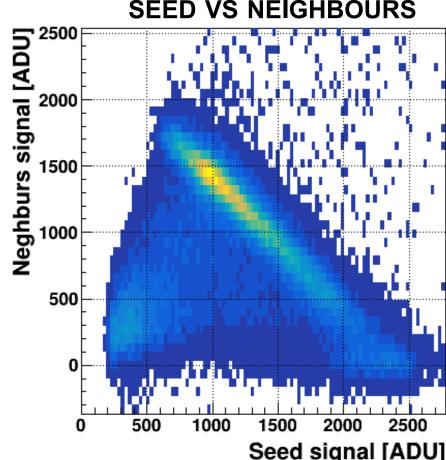




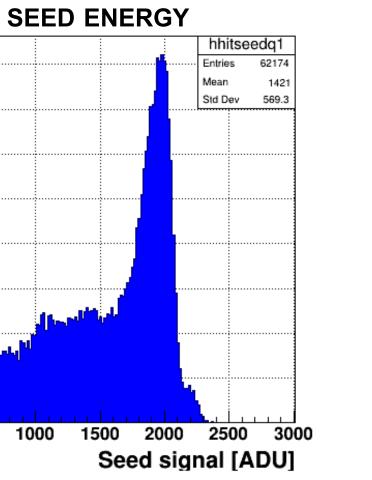


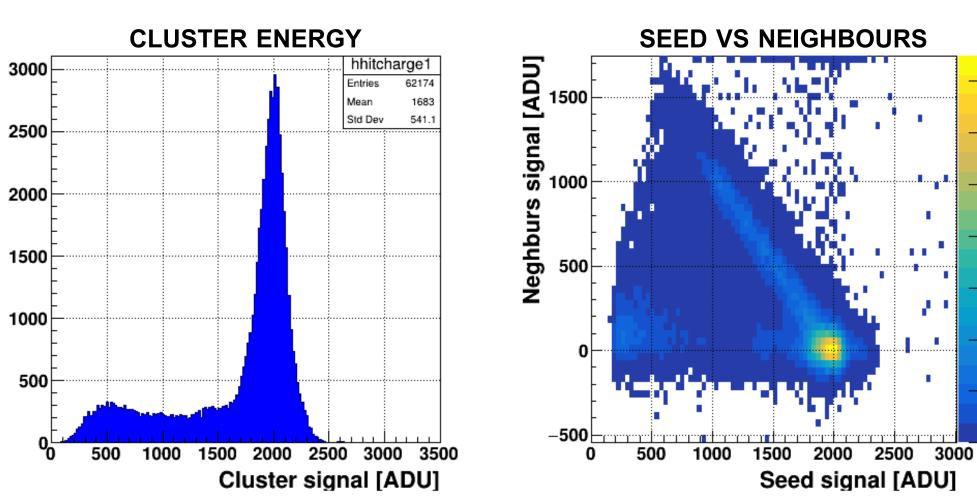
CLUSTER ENERGY



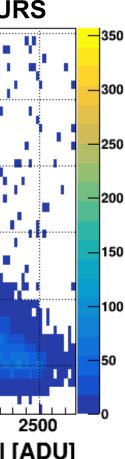


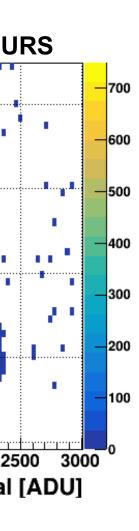
OPTIMIZED DIODE [B4]:



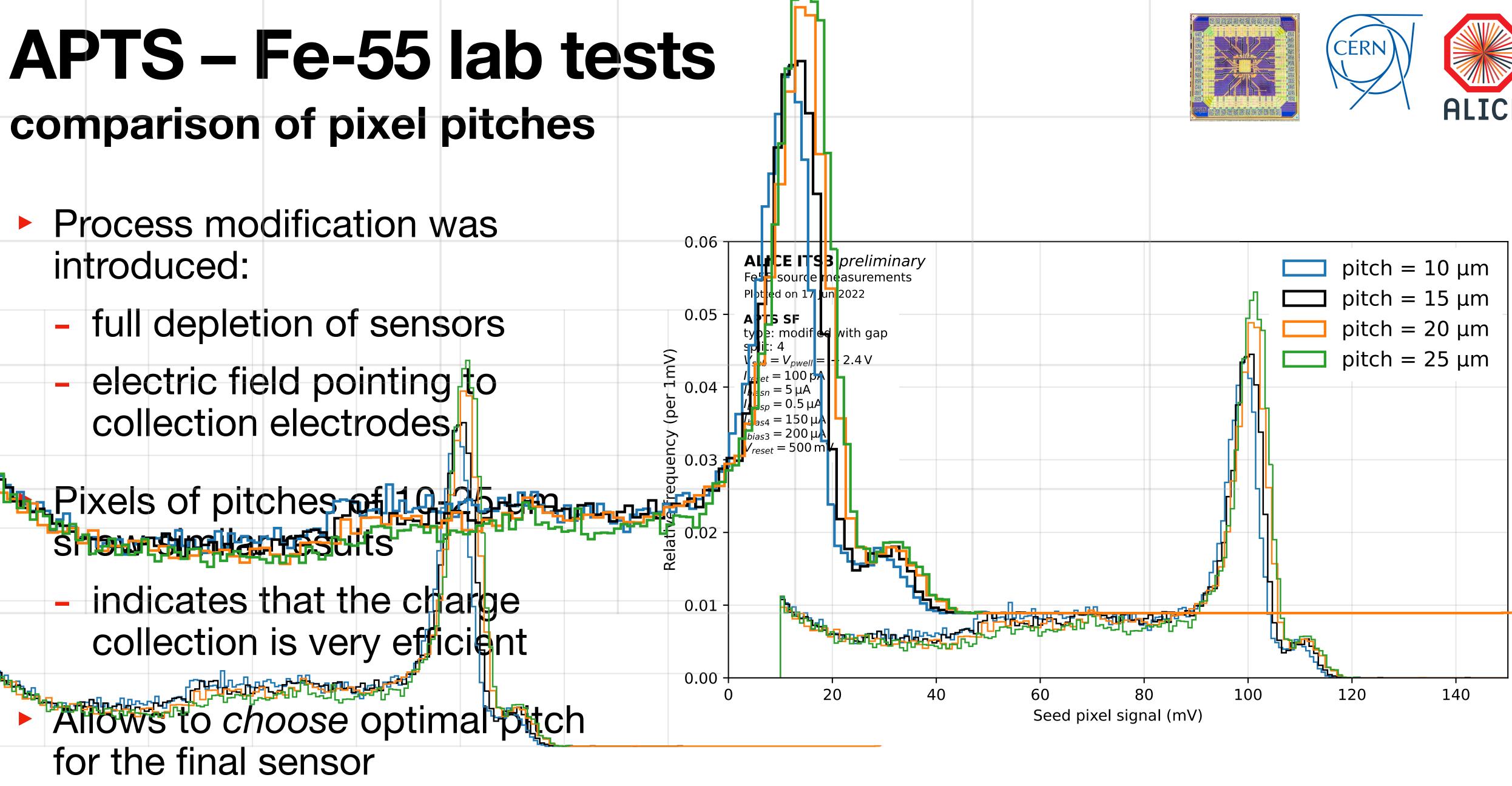








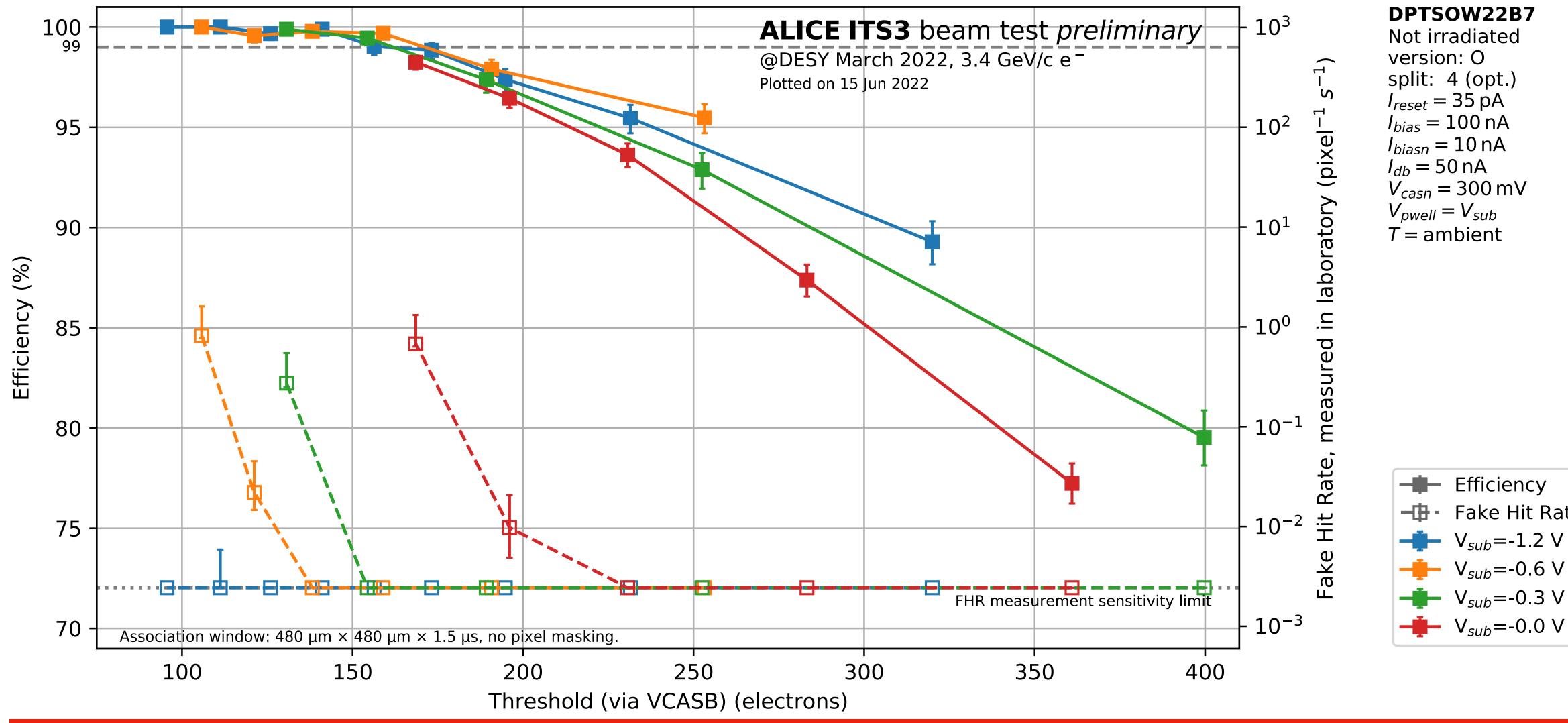
comparison of pixel pitches

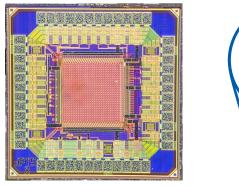


This is a remarkable result — now being verified with beam tests



DPTS – beam tests efficiencies and fake hit rates

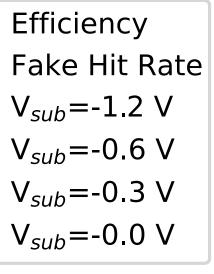






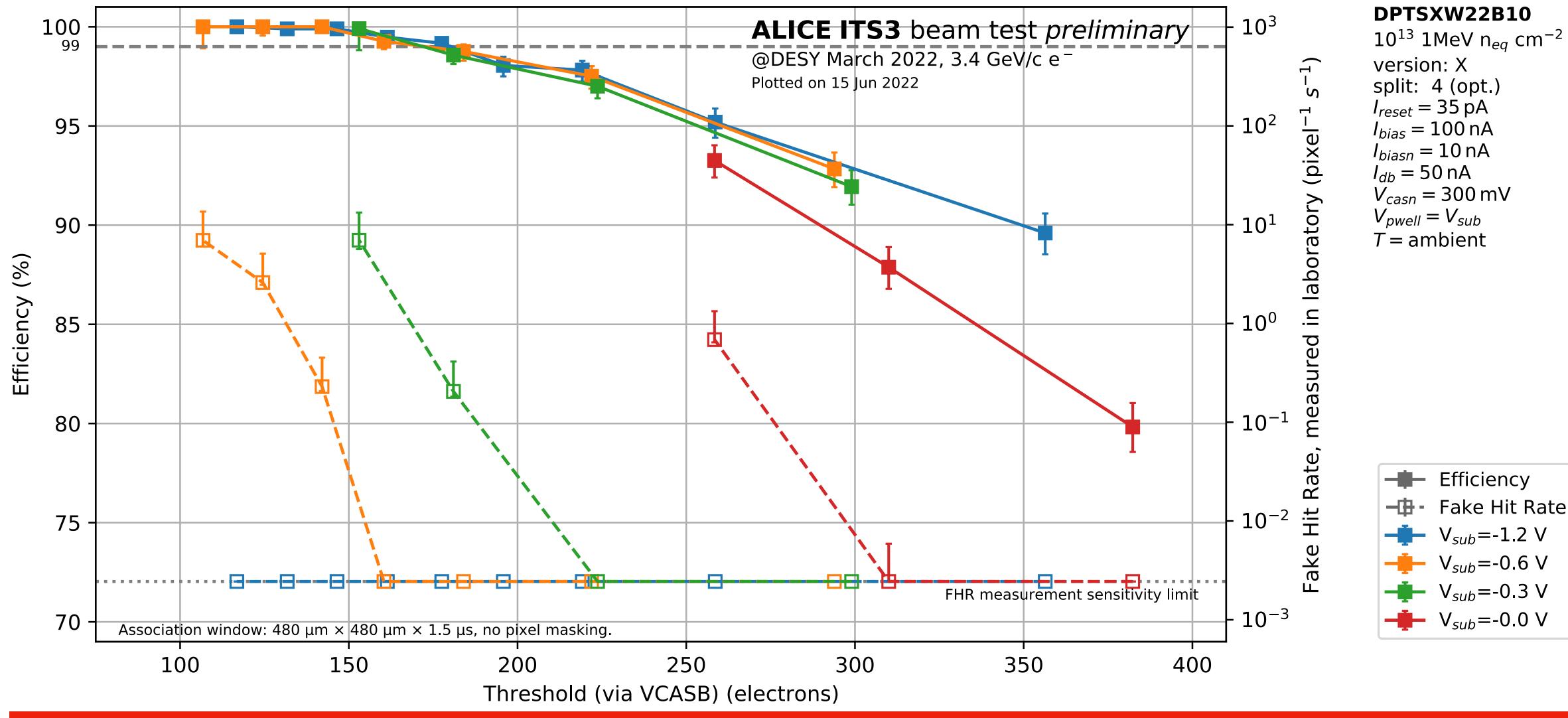
Excellent detection efficiency at very low fake hit rates over large threshold range!

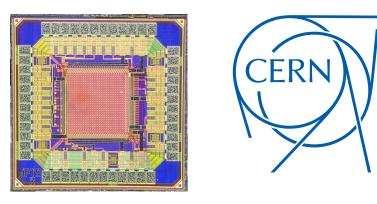






DPTS – beam tests after irradiation: "10¹³ NIEL"

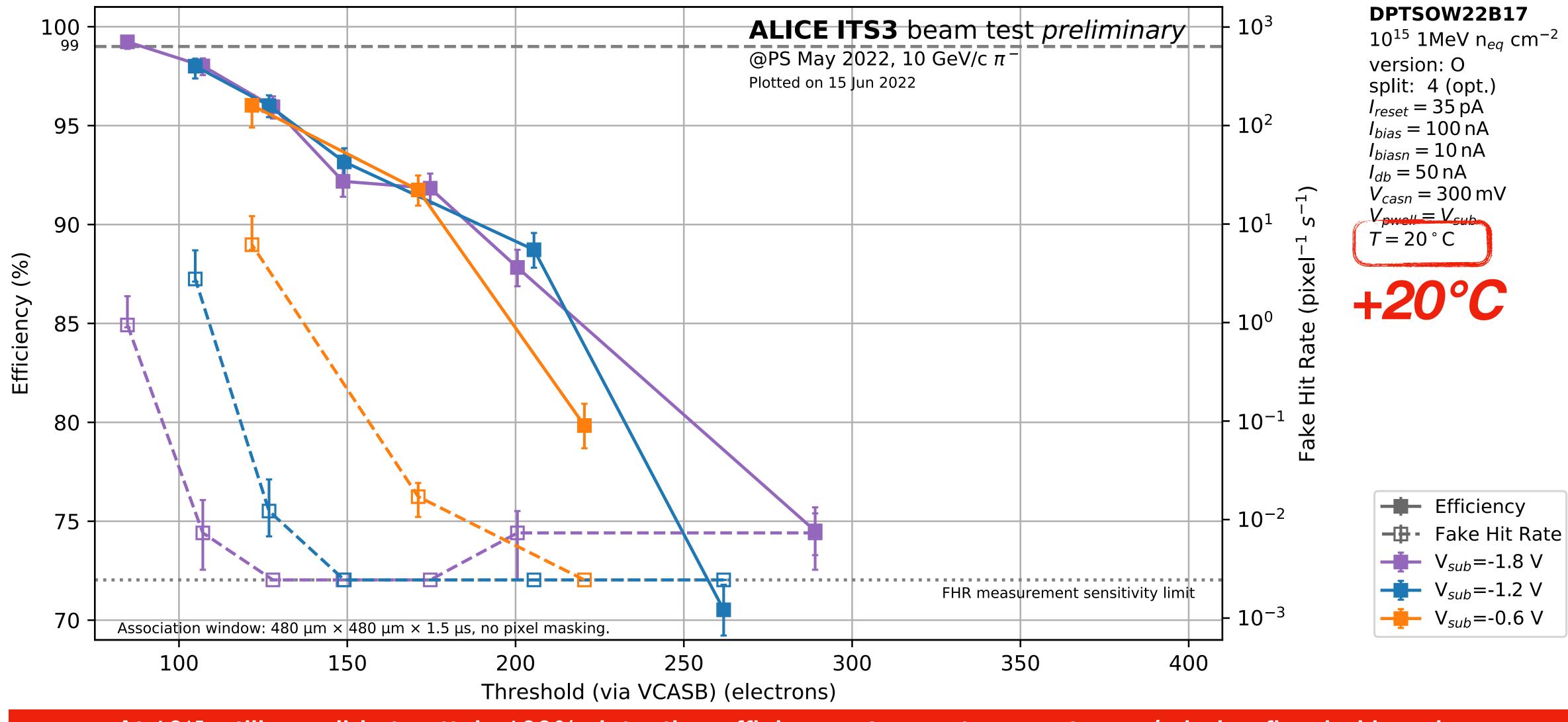




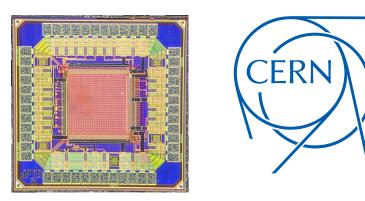
At ALICE conditions: slightly larger fake rates, but still large operational margin



DPTS – beam tests after more irradiation: "10¹⁵ NIEL"



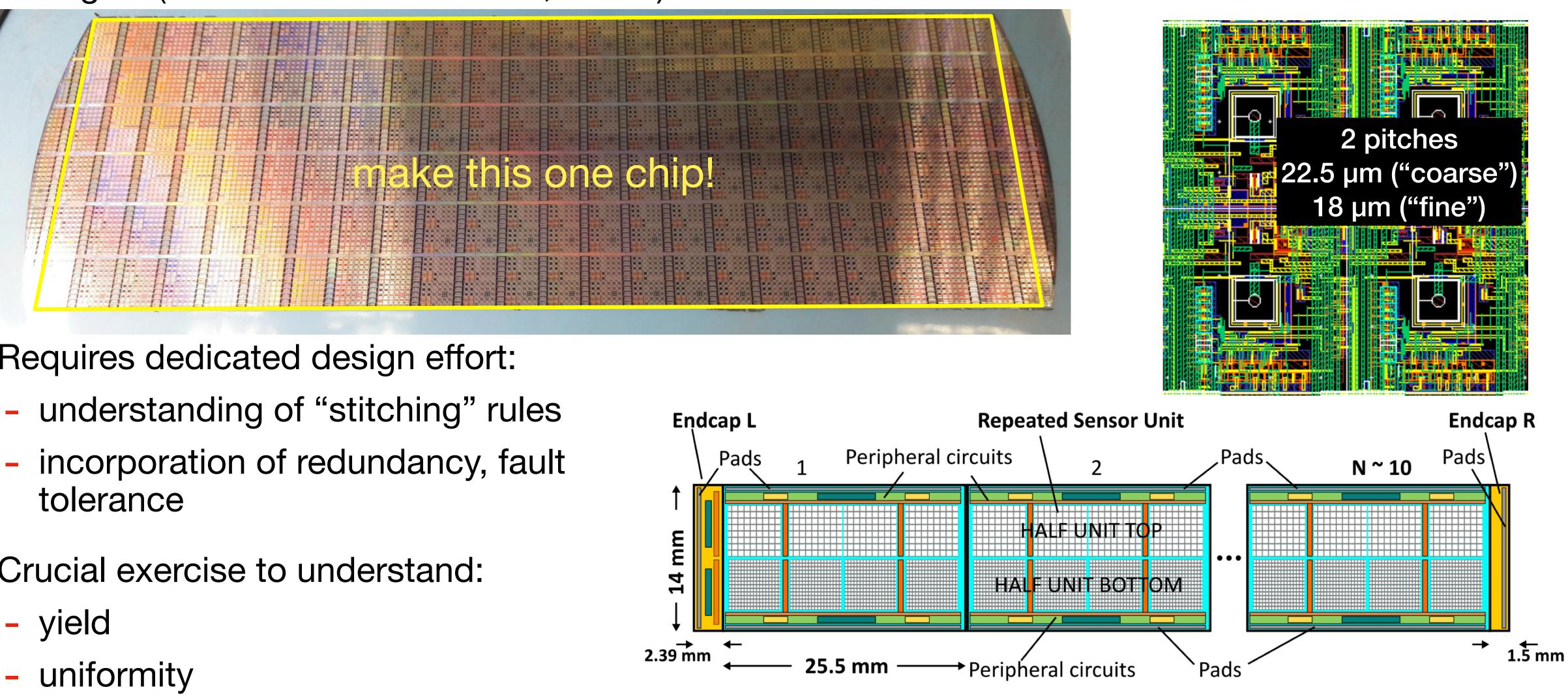
At 10¹⁵: still possible to attain 100% detection efficiency at room temperature w/o being flooded in noise





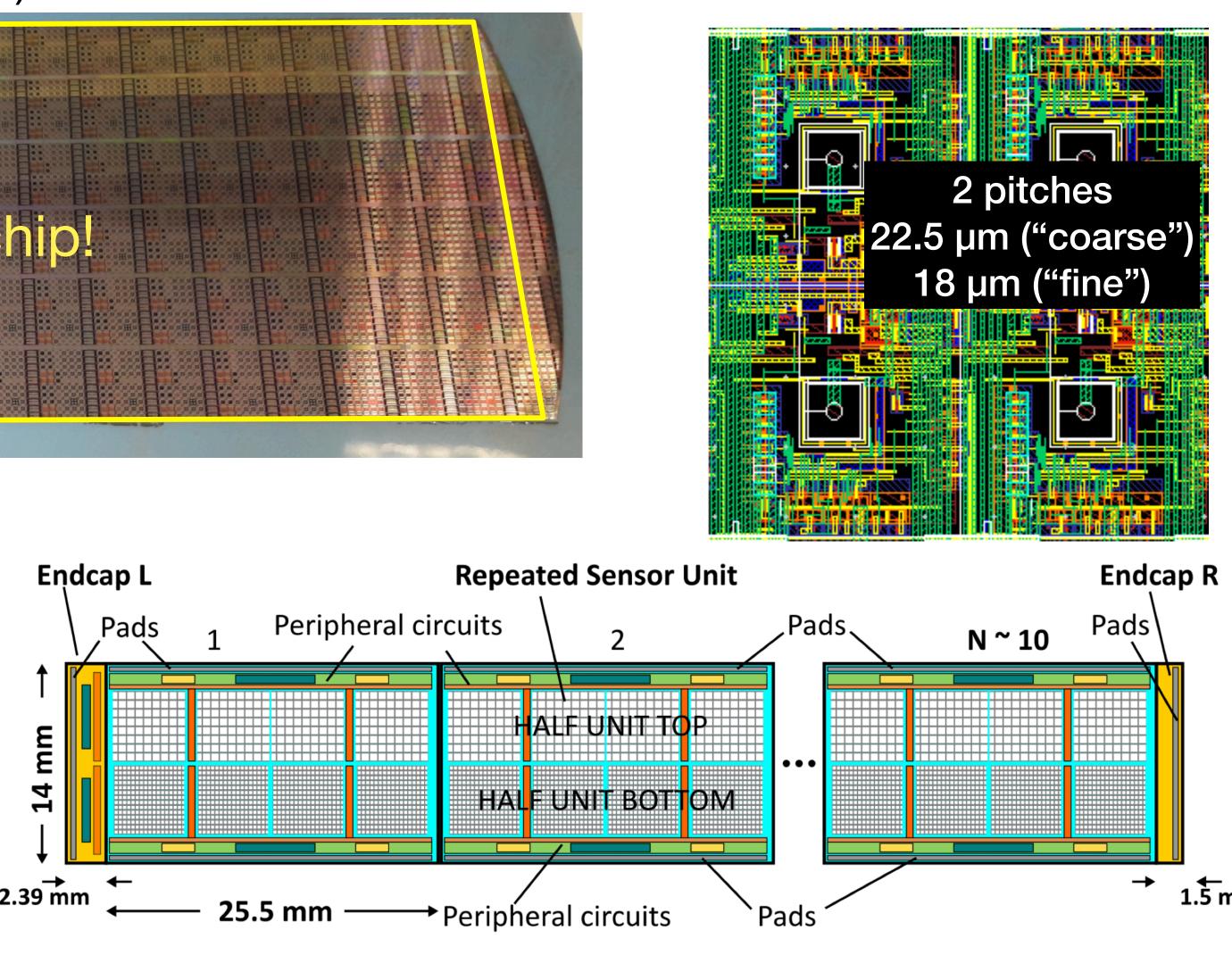
Next chip submission: stitching

Next goal (submission this summer, "ER1"):



Requires dedicated design effort:

- Crucial exercise to understand:





We are taking the next and last critical step!



Summary & Outlook

- ALICE is carrying out the R&D for a new class of vertex detectors target: installation of new inner layers, **ITS3**, for LHC **LS3**
- Large improvement in tracking precision by:
 - new material budget record: < 0.05% X₀ per layer
 - radial distance from IP: only **18 mm**
- Advancing MAPS technology towards:
 - deeper sub micron technology node: 65 nm
 - wafer-scale sensors: **stitching**
- Ultra-thin, bent, wafer-scale MAPS are becoming a reality!
 - for ALICE ITS3, and beyond!







